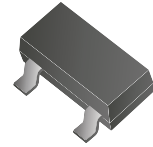


CDSV3-19-G/20-G/21-G

High Speed RoHS Device

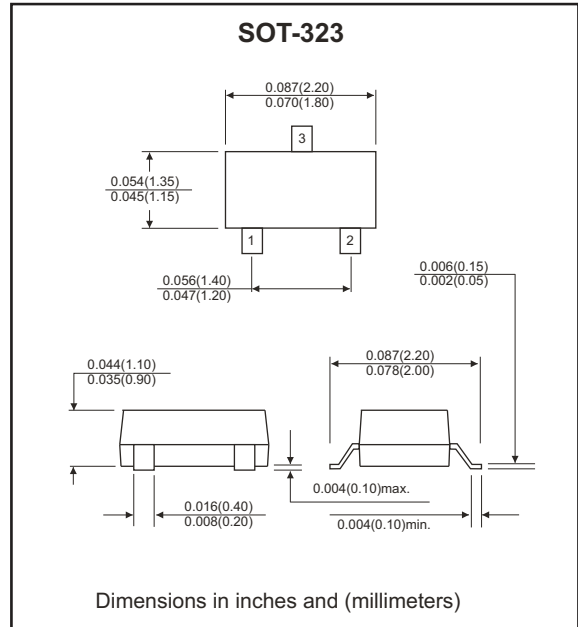
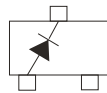


Features

- Fast switching diode.
- Surface mount package ideally for automatic insertion.
- For general purpose switching applications.
- High conductance.

Mechanical data

- Case: SOT-323
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026.
- Marking: CDSV3-19-G KA8
CDSV3-20-G KT2
CDSV3-21-G KT3



Maximum Rating (at Ta=25°C unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|----------------------------------|----------------|---|------|
| Power dissipation | P_D | 200 | mW |
| Forward current | I_F | 200 | mA |
| Reverse voltage | V_R | CDSV3-19-G: 120 CDSV3-20-G: 150 CDSV3-21-G: 200 | V |
| Junction and storage temperature | T_J, T_{STG} | -55 ~ +150 | °C |

Electrical Characteristics (at Ta=25°C unless otherwise noted)

| Parameter | Symbol | Test Conditions | Min | Max | Unit |
|---------------------------|-------------|--|-------------------|-----------|------|
| Reverse breakdown voltage | $V_{(BR)R}$ | $I_R=100\mu A$ | 100 150 200 | | V |
| Reverse leakage current | I_R | $V_R=100V$ $V_R=150V$ $V_R=200V$ | | 0.1 | UA |
| Forward voltage | V_F | $I_F=100mA$ $I_F=200mA$ | | 1 1.25 | V |
| Diode capacitance | C_D | $V_R=0V, f=1MHz$ | | 5 | pF |
| Reverse recovery time | t_{rr} | $I_F=I_R=30mA, I_{rr}=0.1 \times I_R$ | | 50 | nS |

Characteristic Curves (CDSV3-19-G/20-G/21-G)

Fig.1 - Forward Characteristics

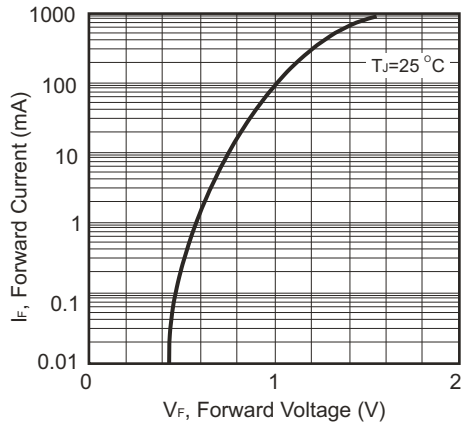


Fig.2 - Leakage Current vs Junction Temperature

